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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Shunpei YAMAZAKI et al.

Serial No. 09/352,194

Filed: July 13, 1999

For: CRYSTALLINE SEMICONDUCTOR

THIN FILM, METHOD OF FABRICATING

THE SAME, SEMICONDUCTOR DEVICE,

AND METHOD OF FABRICATING THE

SAME

) Art Unit: 2823

) Examiner: F. Toledo

**CERTIFICATE OF MAILING**

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**AMENDMENT**

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated June 5, 2002 please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please amend claims 5, 36-48 and 56 as follows:

5. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;

providing said semiconductor film with a catalytic element for facilitating a crystallization of said semiconductor film;

irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film after providing said catalytic element;

removing an oxide film from a surface of said semiconductor film by etching after said irradiation of said laser light;

leveling said surface of said semiconductor film by heating after removing said oxide film; and